

IN THE SPECIFICATION

Please replace the first full paragraph of page 8 with the following:

Fig. 2 illustrates the silicon implantation pre-treatment of the present invention. Silicon ions are implanted 20 into the low-k material layer at an energy of between about 5 and 30 KeV with a dosage of between about 1 E 12 and 1 E 16 ions/cm². The targeted mean depth of implantation is between about 50 and 600 Angstroms. Fig. 3 illustrates the roughened silicon-implanted surface 21 of the low-k material layer 18.

IN THE CLAIMS

Please amend the Claims as follows:

1. (AMENDED) A method of forming a dielectric material layer comprising:
depositing a low dielectric constant material layer on a substrate wherein said low dielectric constant material comprises: porous or non-porous carbon-based silicon oxides, porous or non-porous doped silicon oxides, porous or non-porous organic polymers, or porous